



STPS10L60CF/CFP

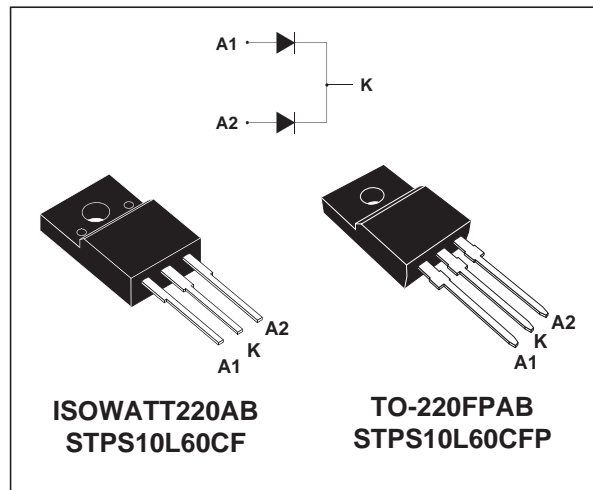
POWER SCHOTTKY RECTIFIER

MAIN PRODUCT CHARACTERISTICS

| | |
|-------------|---------|
| $I_{F(AV)}$ | 2 x 5 A |
| V_{RRM} | 60 V |
| $T_j(max)$ | 150 °C |
| $V_F(max)$ | 0.52 V |

FEATURES AND BENEFITS

- LOW FORWARD VOLTAGE DROP
- NEGLIGIBLE SWITCHING LOSSES
- INSULATED PACKAGE:
Insulating voltage = 2000V DC
Capacitance = 12pF
- AVALANCHE CAPABILITY SPECIFIED



DESCRIPTION

Dual center tap Schottky rectifiers suited for Switched Mode Power Supplies and high frequency DC to DC converters.

Packaged in ISOWATT220AB, TO-220FPAB this device is intended for use in high frequency inverters.

ABSOLUTE RATINGS (limiting values, per diode)

| Symbol | Parameter | | | Value | Unit | |
|--------------|--|---------------------------|--|-------------------------|------------------|---|
| V_{RRM} | Repetitive peak reverse voltage | | | 60 | V | |
| $I_{F(RMS)}$ | RMS forward current | | | 30 | A | |
| $I_{F(AV)}$ | Average forward current | ISOWATT220AB TO220FPAB | $T_c = 130^\circ\text{C}$ $\delta = 0.5$ | Per diode Per device | 5 10 | A |
| I_{FSM} | Surge non repetitive forward current | | $t_p = 10 \text{ ms}$ Sinusoidal | 180 | A | |
| I_{RRM} | Repetitive peak reverse current | | $t_p = 2 \mu\text{s}$ square F = 1kHz | 1 | A | |
| P_{ARM} | Repetitive peak avalanche power | | $t_p = 1 \mu\text{s}$ $T_j = 25^\circ\text{C}$ | 4000 | W | |
| T_{stg} | Storage temperature range | | | - 65 to + 175 | °C | |
| T_j | Maximum operating junction temperature * | | | 150 | °C | |
| dV/dt | Critical rate of rise reverse voltage | | | 10000 | V/ μs | |

* : $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ thermal runaway condition for a diode on its own heatsink

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THERMAL RESISTANCE

| Symbol | Parameter | | Value | Unit |
|---------------|--|-----------|-------|------|
| $R_{th(j-c)}$ | Junction to case ISOWATT220AB TO-220FPAB | Per Diode | 4.5 | °C/W |
| | | Total | 3.5 | |
| $R_{th(c)}$ | | Coupling | 2.5 | °C/W |

When the diodes 1 and 2 are used simultaneously :
 $\Delta T_j(\text{diode } 1) = P(\text{diode } 1) \times R_{th(j-c)}(\text{Per diode}) + P(\text{diode } 2) \times R_{th(c)}$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

| Symbol | Parameter | Tests conditions | | Min. | Typ. | Max. | Unit | |
|---------|-------------------------|---------------------------|--------------------|---------------------|------|------|---------------|------|
| I_R^* | Reverse leakage current | $T_j = 25^\circ\text{C}$ | $V_R = V_{RRM}$ | | | 220 | μA | |
| | | $T_j = 125^\circ\text{C}$ | | | 45 | 60 | mA | |
| V_F^* | Forward voltage drop | $T_j = 25^\circ\text{C}$ | $I_F = 5\text{ A}$ | | | 0.55 | V | |
| | | $T_j = 125^\circ\text{C}$ | | | 0.43 | 0.52 | | |
| | | $T_j = 25^\circ\text{C}$ | | $I_F = 10\text{ A}$ | | | | 0.67 |
| | | $T_j = 125^\circ\text{C}$ | | | | 0.55 | | 0.64 |

Pulse test : * $t_p = 380\ \mu\text{s}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation :
 $P = 0.4 \times I_{F(AV)} + 0.024 \times I_{F(RMS)}^2$

Fig. 1: Average forward power dissipation versus average forward current (per diode).

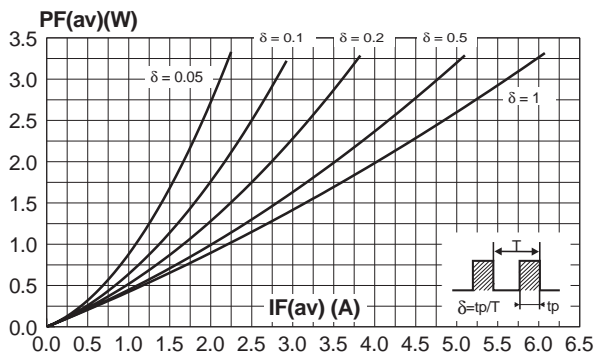


Fig. 2: Average current versus ambient temperature ($\delta=0.5$) (per diode).

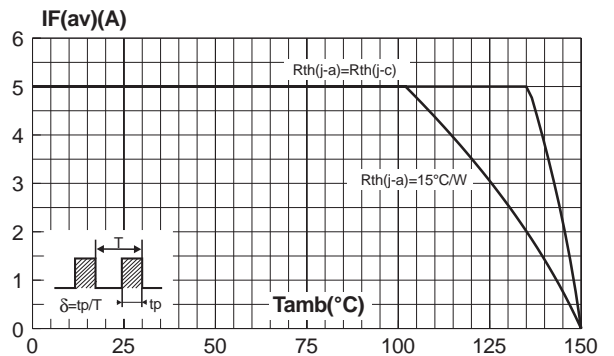


Fig. 3: Normalized avalanche power derating versus pulse duration.

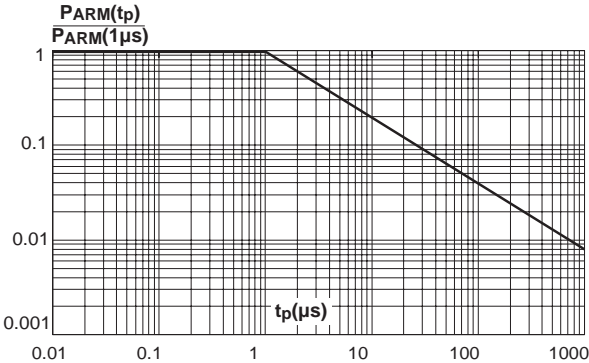


Fig. 4: Normalized avalanche power derating versus junction temperature.

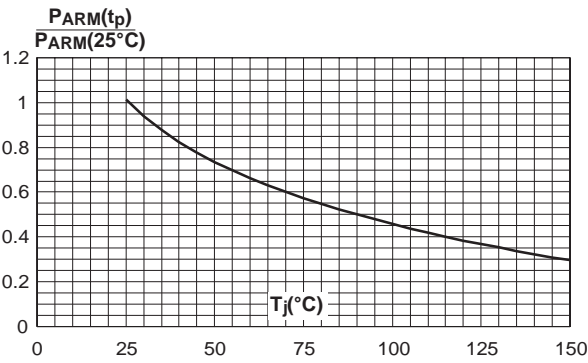


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values, per diode) (ISOWATT220AB, TO-220FPAB).

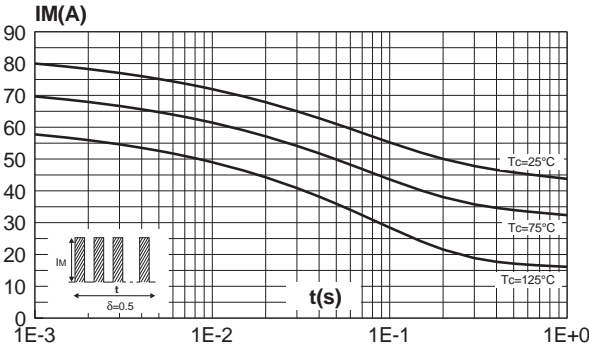


Fig. 6: Relative variation of thermal transient impedance junction to case versus pulse duration. (ISOWATT220AB, TO-220FPAB).

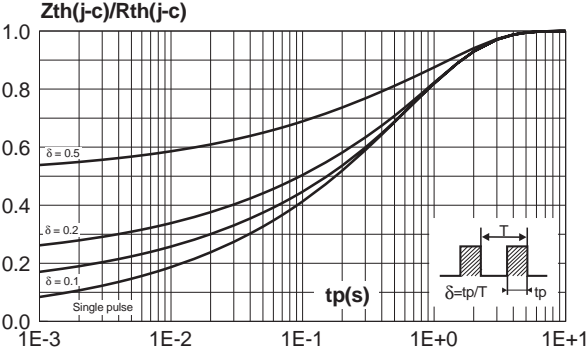


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values, per diode).

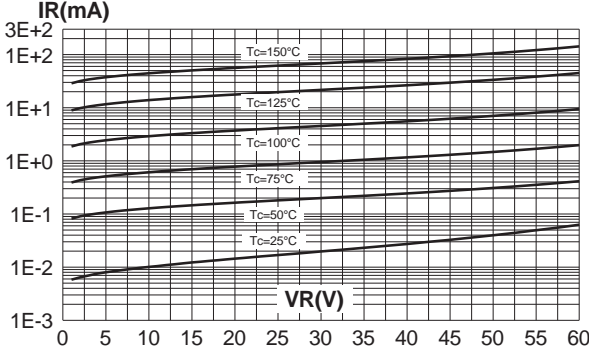
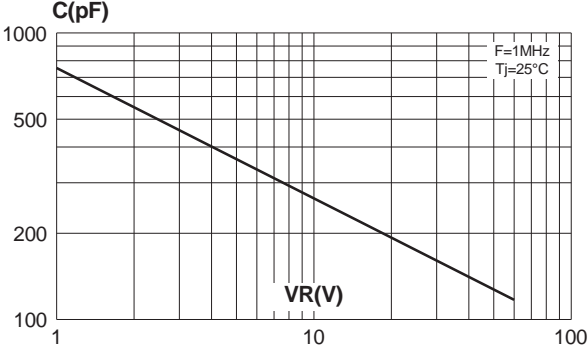
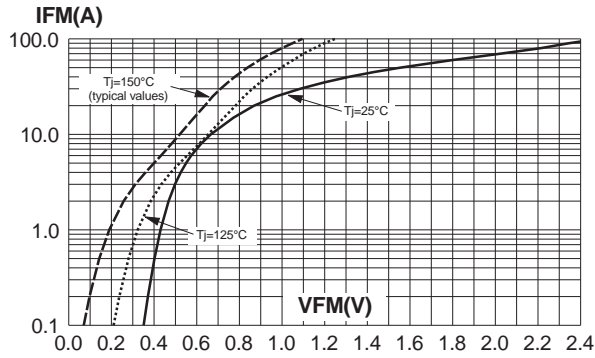


Fig. 8: Junction capacitance versus reverse voltage applied (typical values, per diode).

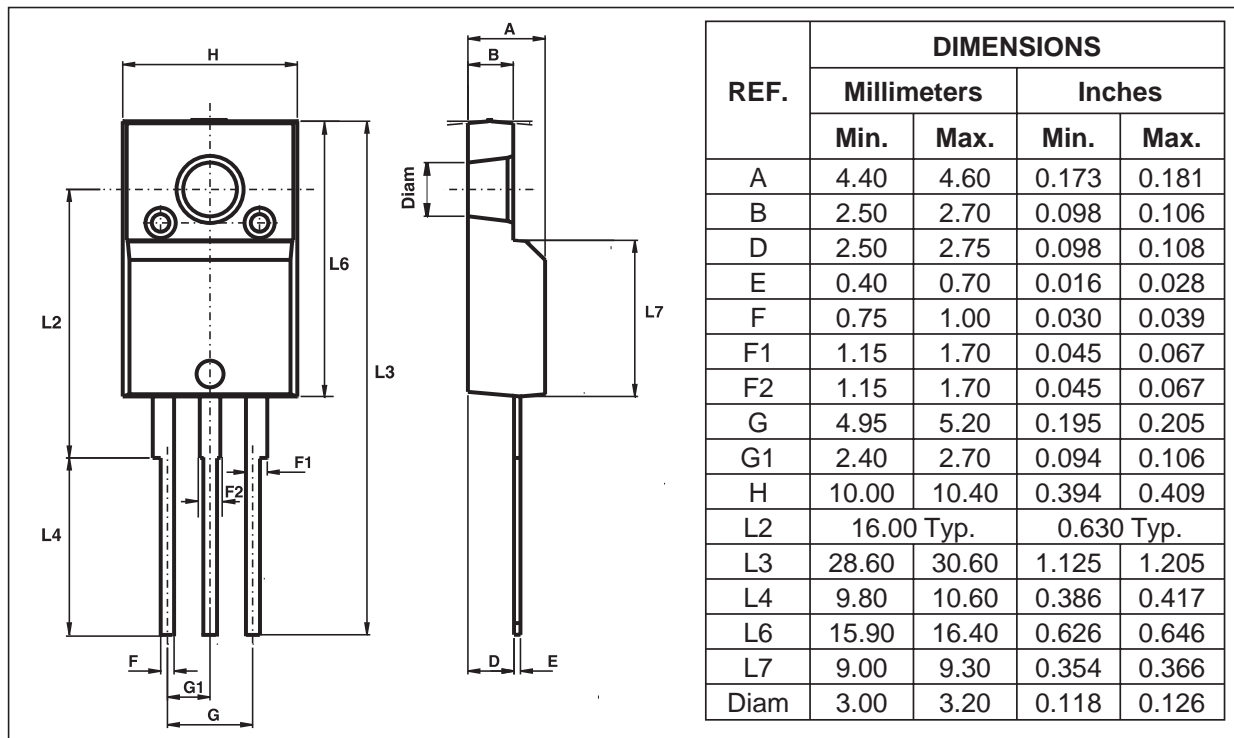


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Fig. 9: Forward voltage drop versus forward current (maximum values, per diode).



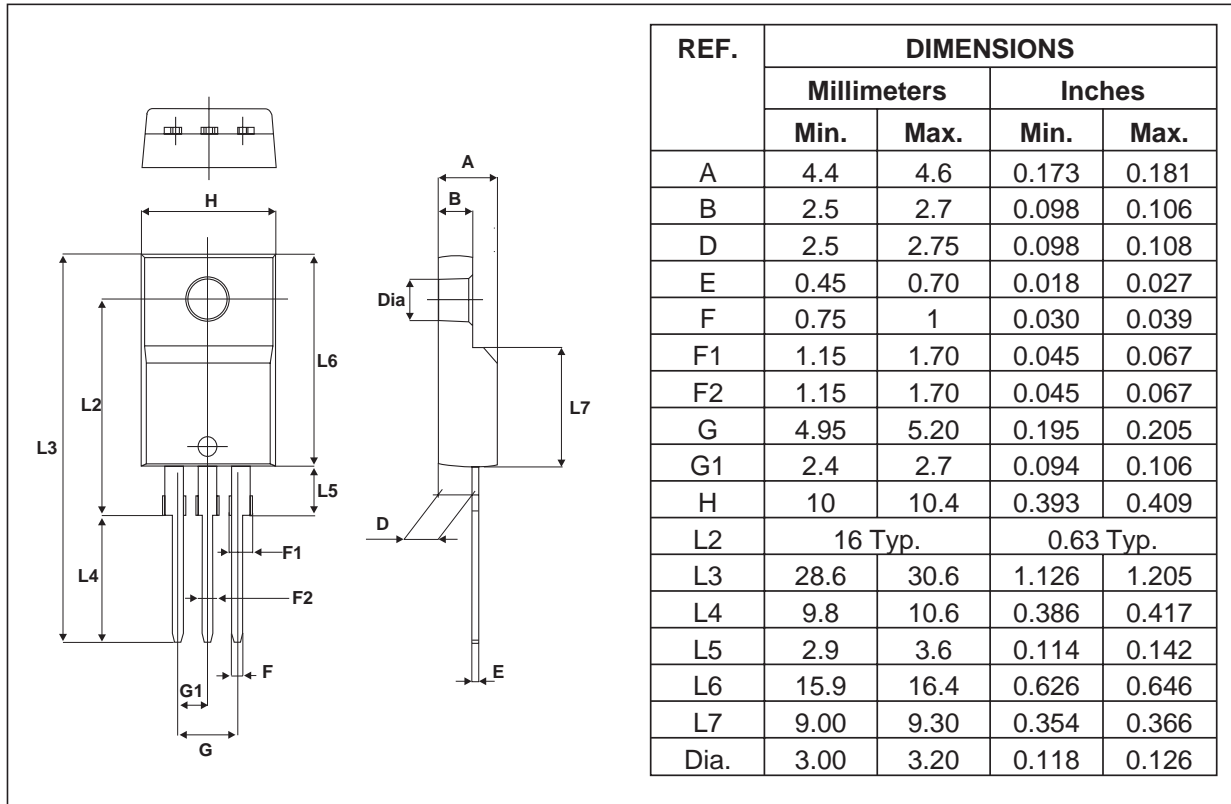
PACKAGE MECHANICAL DATA ISOWATT220AB



- Cooling method: C
- Recommended torque value: 0.55 m.N
- Maximum torque value: 0.70 m.N

PACKAGE MECHANICAL DATA

TO-220FPAB



| Ordering type | Marking | Package | Weight | Base qty | Delivery mode |
|---------------|--------------|--------------|--------|----------|---------------|
| STPS10L60CF | STPS10L60CF | ISOWATT220AB | 2.08g | 50 | Tube |
| STPS10L60CF | STPS10L60CF | ISOWATT220AB | 2.08g | 1000 | Bulk |
| STPS10L60CFP | STPS10L60CFP | TO-220FPAB | 2 g | 50 | Tube |

- Epoxy meets UL94,V0

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